Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# **MT3S16FS**

VHF~UHF Band Oscillator and Amplifier Applications

- f<sub>T</sub> is high and current dependability is excellent.
- The Cre curve is flat.

:NF = 2.4 dB (@ 2V, 5mA,1GHz)

 $|S_{21e}|^2 = 4.5 \text{ dB } (@ 2V, 10mA, 1GHz)$ 

## Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector- base voltage	$V_{CBO}$	10	V
Collector- emitter voltage	V <sub>CEO</sub>	5	V
Emitter- base voltage	V <sub>EBO</sub>	2	V
Collector current	IC	60	mA
Base current	Ι <sub>Β</sub>	10	mW
Collector power dissipation	P <sub>C</sub> (Note)	85	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C

1.Base fSM 2.Emitter 3.Collector

JEDEC —

JEITA —

TOSHIBA 2-1E1A

Weight: 0.0006g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook

("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note: 10 mm<sup>2</sup> × 1.0 mm (t), mounted on a glass-epoxy printed circuit board.

## Marking



2007-11-01



# Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Condition	Min	Тур.	Max	Unit
Transition frequency	f <sub>T</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$	2	4	_	GHz
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 2 \text{ V}, I_{C} = 10 \text{ mA}, f = 1 \text{ GHz}$	_	4.5	_	dB
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, I_{C} = 30 \text{ mA}, f = 1 \text{ GHz}$	3	5.5	_	
Noise figure	NF	$V_{CE} = 2 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	_	2.4	3.2	dB

## **Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Condition	Min	Тур.	Max	Unit
Collector cutoff current	ICBO	V <sub>CB</sub> = 5 V, I <sub>E</sub> = 0	_	_	0.1	μА
Emitter cutoff current	I <sub>EBO</sub>	$V_{EB} = 1 \text{ V}, I_{C} = 0$		_	1	μΑ
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA	80	_	140	_
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB} = 1 \text{ V}, I_{E} = 0, f = 1 \text{ MHz(Note)}$	_	2.4	3	pF

Note: Cre is measured with a three-terminal method using a capacitance bridge.

### Caution

This device is sensitive to electrostatic discharge. Ensure that tools and equipment are sufficiently grounded before handling. When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

#### **RESTRICTIONS ON PRODUCT USE**

20070701-EN GENERAL

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